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- (71) **Applicant (for all designated States except US):** MICRON TECHNOLOGY, INC. [US/US]; 8000 S. Federal Way, Boise, Idaho 83707-0006 (US).
- (72) **Inventor; and**
- (75) **Inventor/Applicant (for US only):** CAMPBELL, Kristy, A. [US/US]; P.O. Box 191171, Boise, Idaho 83719 (US).
- (74) **Agent:** D'AMICO, Thomas, J.; Dickstein Shapiro Morin & Oshinsky LLP, 2101 L Street Nw, Washington, DC 20037-1526 (US).

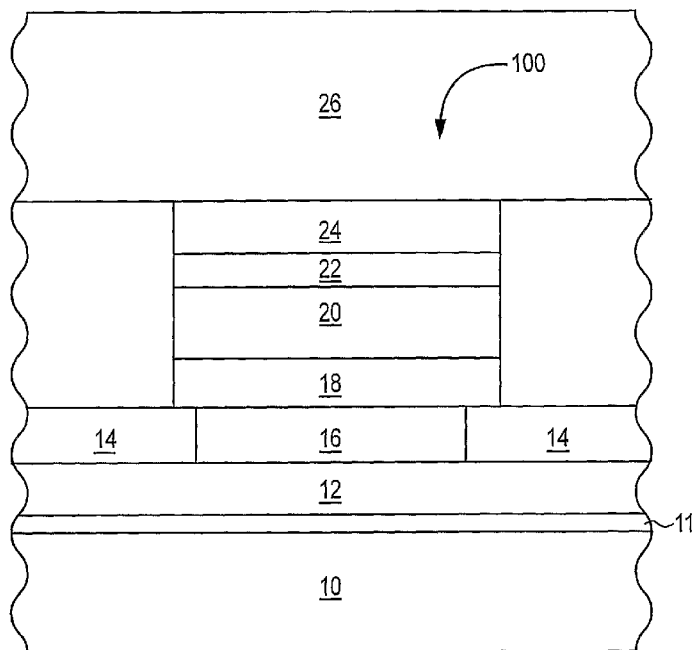
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(54) **Title:** SNSE-BASED LIMITED REPROGRAMMABLE CELL



(57) **Abstract:** Methods and apparatus for providing a memory device that can be programmed a limited number of times. According to exemplary embodiments, a memory device and its method of formation provide a first electrode, a second electrode and a layer of a chalcogenide or germanium comprising material between the first electrode and the second electrode. The memory device further includes a tin-chalcogenide layer between the chalcogenide or germanium comprising material layer and the second electrode.

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